

# GaAs-IR-Lumineszenzdiode mit Zylinderlinse (950nm) GaAs Infrared Emitter with cylindrical lens (950nm)

SFH 4111



## Wesentliche Merkmale

- Wellenlänge der Strahlung 950 nm
- Zylinderlinse
- Hohe Strahlstärke
- Geringe Außenabmessungen

## Features

- Peak wavelength of 950 nm
- Cylindrical lens
- High radiant intensity
- Small outline dimensions

## Anwendungen

- Bandende Erkennung (z.B. Videorecorder)
- Datenübertragung
- Positionsüberwachung
- Barcode-Leser
- „Messen/Steuern/Regeln“
- Münzzähler

## Applications

- Tape end detection (VCR e.g.)
- Data transmission
- Position sensing
- Barcode reader
- For control and drive circuits
- Coin counters

| Typ<br>Type | Bestellnummer<br>Ordering Code | Ee <sup>1)</sup> [mW/cm <sup>2</sup> ]<br>at d <sup>2)</sup> =6mm, If=4mA |
|-------------|--------------------------------|---------------------------------------------------------------------------|
| SFH 4111    | Q62702-P5333                   | 0.25 - 1                                                                  |

<sup>1)</sup> Auf einem Detektor erzeugte Bestrahlungsstärke.  
Irradiance generated on a detector.

<sup>2)</sup> Entfernung zwischen Vorderseite Beinchen und Detektorebene.  
Distance between leadframe front side and detection area.

**Grenzwerte** ( $T_A = 25\text{ °C}$ )**Maximum Ratings**

| Bezeichnung<br>Parameter                                                         | Symbol<br>Symbol  | Wert<br>Value | Einheit<br>Unit |
|----------------------------------------------------------------------------------|-------------------|---------------|-----------------|
| Betriebs- und Lagertemperatur<br>Operating and storage temperature range         | $T_{op}; T_{stg}$ | - 40 ... + 85 | °C              |
| Sperrspannung<br>Reverse voltage                                                 | $V_R$             | 5             | V               |
| Durchlaßstrom<br>Forward current                                                 | $I_F$ (DC)        | 50            | mA              |
| Stoßstrom, $t_p = 10\text{ }\mu\text{s}$ , $D = 0$<br>Surge current              | $I_{FSM}$         | 1             | A               |
| Verlustleistung<br>Power dissipation                                             | $P_{tot}$         | 75            | mW              |
| Wärmewiderstand Sperrschicht - Umgebung<br>Thermal resistance junction - ambient | $R_{thJA}$        | 450           | K/W             |

**Kennwerte** ( $T_A = 25\text{ °C}$ )**Characteristics**

| Bezeichnung<br>Parameter                                                                                                                                                                                                    | Symbol<br>Symbol             | Wert<br>Value    | Einheit<br>Unit |
|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------------------------|------------------|-----------------|
| Wellenlänge der Strahlung<br>Wavelength at peak emission                                                                                                                                                                    | $\lambda_{peak}$             | 950              | nm              |
| Spektrale Bandbreite bei 50% von $I_{max}$<br>Spectral bandwidth at 50% of $I_{max}$                                                                                                                                        | $\Delta\lambda$              | 55               | nm              |
| Abstrahlwinkel horizontal/ vertikal<br>Half angle horizontal/ vertical                                                                                                                                                      | $\varphi$                    | $\pm 30/ 60$     | Grad<br>deg.    |
| Aktive Chipfläche<br>Active chip area                                                                                                                                                                                       | A                            | 0.09             | mm <sup>2</sup> |
| Abmessungen der aktiven Chipfläche<br>Dimensions of the active chip area                                                                                                                                                    | $L \times B$<br>$L \times W$ | $0.3 \times 0.3$ | mm              |
| Schaltzeiten, $I_e$ von 10% auf 90% und von 90% auf 10%, bei $I_F = 50\text{ mA}$ , $R_L = 50\text{ }\Omega$<br>Switching times, $I_e$ from 10% to 90% and from 90% to 10%, $I_F = 50\text{ mA}$ , $R_L = 50\text{ }\Omega$ | $t_r, t_f$                   | 0.5              | $\mu\text{s}$   |
| Kapazität,<br>Capacitance<br>$V_R = 0\text{ V}$ , $f = 1\text{ MHz}$                                                                                                                                                        | $C_o$                        | 40               | pF              |

**Kennwerte** ( $T_A = 25\text{ °C}$ )**Characteristics** (cont'd)

| Bezeichnung<br>Parameter                                                                                                  | Symbol<br>Symbol | Wert<br>Value       | Einheit<br>Unit |
|---------------------------------------------------------------------------------------------------------------------------|------------------|---------------------|-----------------|
| Durchlaßspannung,<br>Forward voltage<br>$I_F = 20\text{ mA}$ , $t_p = 20\text{ ms}$                                       | $V_F$            | 1.25 ( $\leq 1.6$ ) | V               |
| Sperrstrom,<br>Reverse current<br>$V_R = 5\text{ V}$                                                                      | $I_R$            | 0.01 ( $\leq 1.0$ ) | $\mu\text{A}$   |
| Gesamtstrahlungsfluß,<br>Total radiant flux<br>$I_F = 20\text{ mA}$ , $t_p = 20\text{ ms}$                                | $\Phi_e$         | 3.5                 | mW              |
| Temperaturkoeffizient von $I_e$ bzw. $\Phi_e$ ,<br>Temperature coefficient of $I_e$ or $\Phi_e$ ,<br>$I_F = 4\text{ mA}$  | $TC_I$           | - 1.1               | %/K             |
| Temperaturkoeffizient von $V_F$ , $I_F = 4\text{ mA}$<br>Temperature coefficient of $V_F$ , $I_F = 4\text{ mA}$           | $TC_V$           | - 1.3               | mV/K            |
| Temperaturkoeffizient von $\lambda$ , $I_F = 10\text{ mA}$<br>Temperature coefficient of $\lambda$ , $I_F = 10\text{ mA}$ | $TC_\lambda$     | + 0.3               | nm/K            |

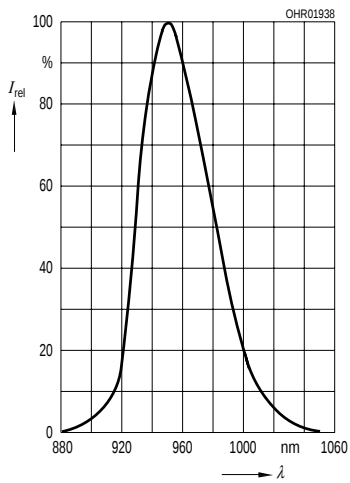
| Bezeichnung<br>Parameter                                                                                                          | Symbol      | Werte<br>Values | Einheit<br>Unit    |
|-----------------------------------------------------------------------------------------------------------------------------------|-------------|-----------------|--------------------|
| Bestrahlungsstärke <sup>1)</sup><br>Irradiance <sup>1)</sup><br>$d^2) = 6\text{ mm}$ , $I_F = 4\text{ mA}$ , $t_p = 20\text{ ms}$ | $E_e^{(1)}$ | 0.25 ... 1      | mW/cm <sup>2</sup> |

<sup>1)</sup> Auf einem Detektor erzeugte Bestrahlungsstärke<sup>1)</sup>  
Irradiance generated on a detector.

<sup>2)</sup> Entfernung zwischen Vorderseite Beinchen und Detektorebene.  
Distance between leadframe front side and detection area.

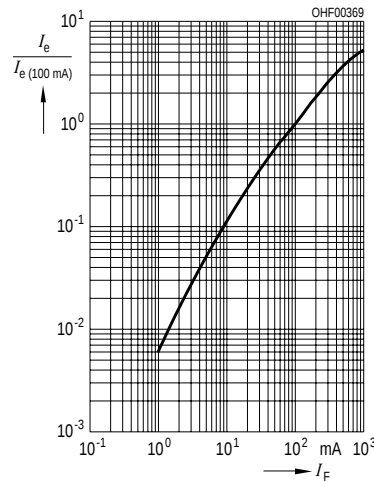
### Relative Spectral Emission

$$I_{\text{rel}} = f(\lambda)$$



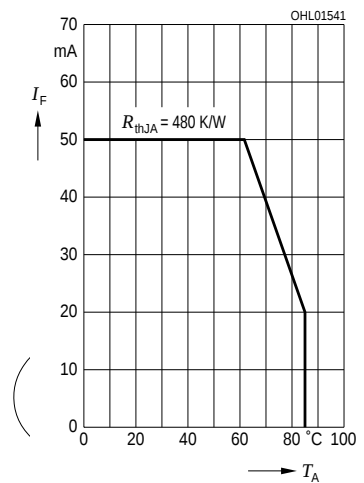
$$\text{Radiant Intensity } \frac{I_e}{I_e(100 \text{ mA})} = f(I_F)$$

Single pulse,  $t_p = 20 \mu\text{s}$



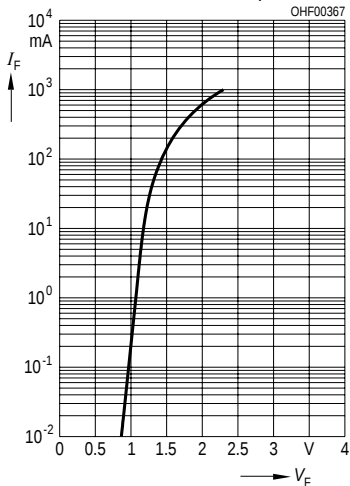
### Max. Permissible Forward Current

$$I_F = f(T_A)$$



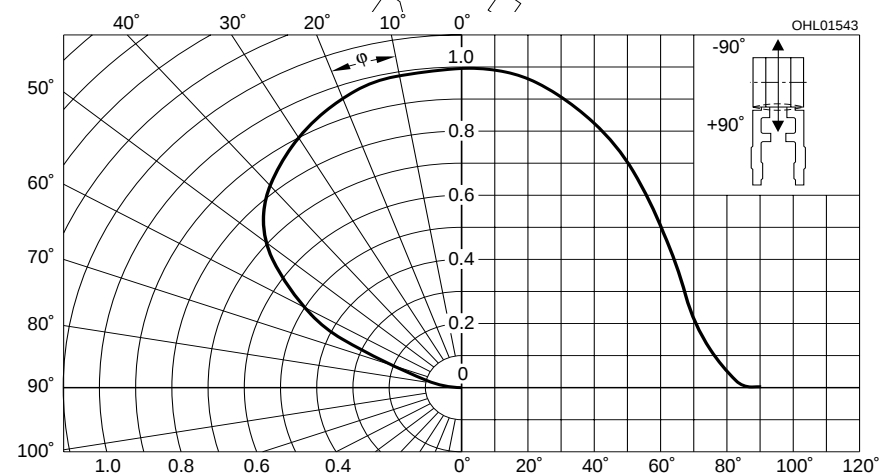
### Forward Current

$$I_F = f(V_F), \text{ Single pulse, } t_p = 20 \mu\text{s}$$



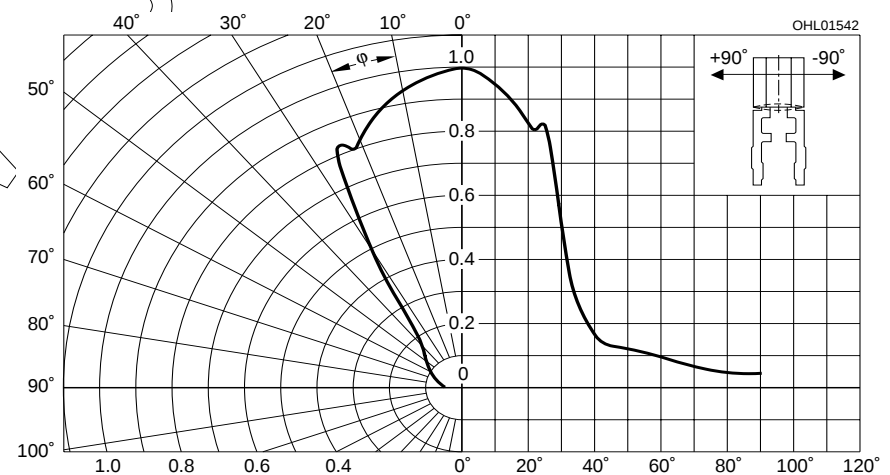
### Radiation Characteristics/ vertical

$$I_{\text{rel}} = f(\varphi)$$

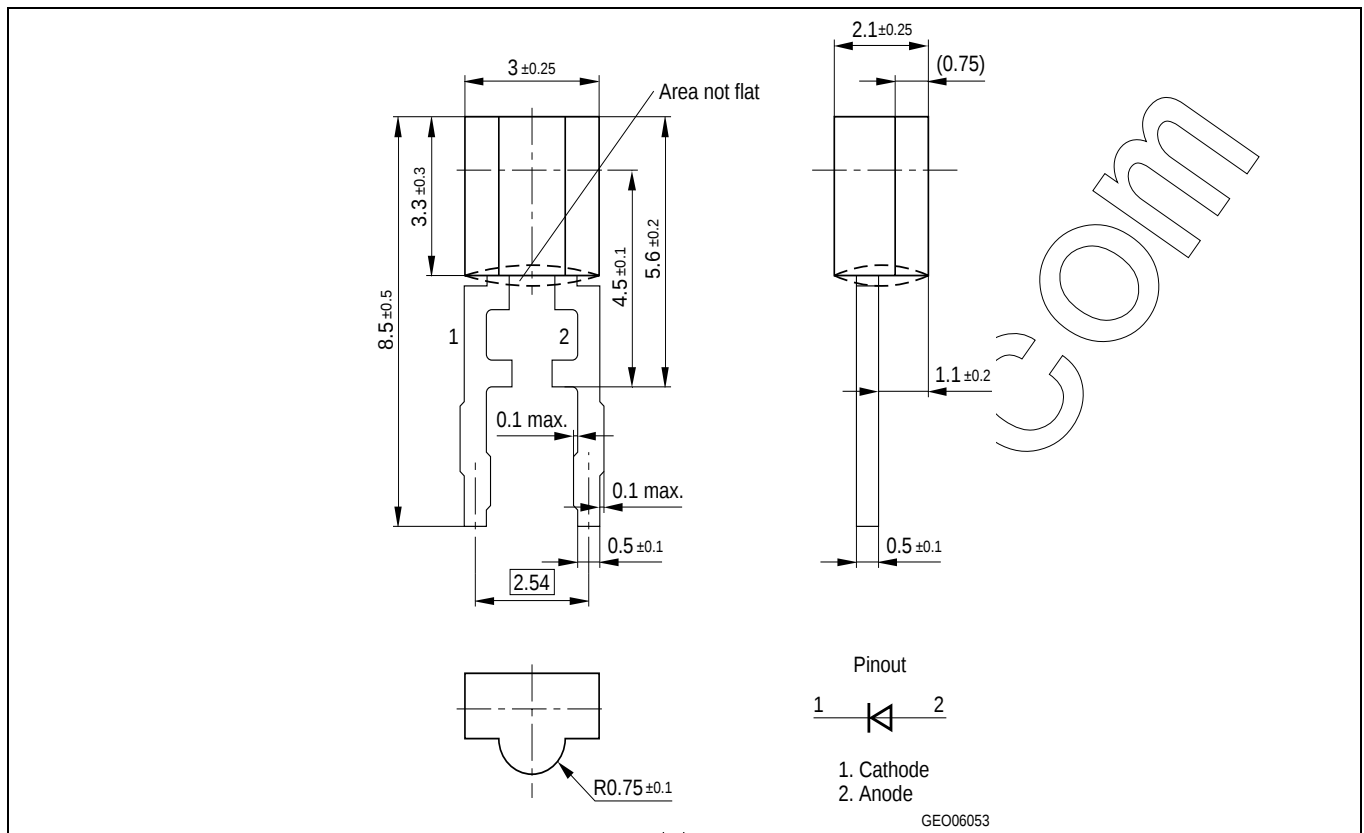


### Radiation Characteristics/ horiz.

$$I_{\text{rel}} = f(\varphi)$$



## Maßzeichnung Package Outlines



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

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